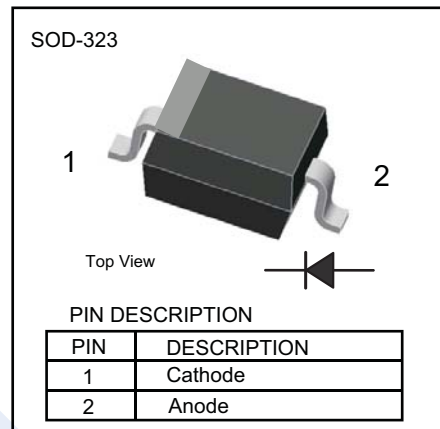


## Schottky Diodes

### 1N5817WSB-1N5819WSB

#### ■ Features

- Low Positive Pressure Drop.
- Can Ignore the Reverse Recovery Time.



#### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating			Unit
		1N5819WSB	1N5818WSB	1N5817WSB	
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>				V
Working Peak Reverse Voltage	V <sub>RWM</sub>	40	30	20	
DC Reverse Voltage	V <sub>R</sub>				
RMS Reverse Voltage	V <sub>R(RMS)</sub>	28	21	14	
Non-Repetitive Peak Forward Current	I <sub>FM</sub>	350			mA
Non-Repetitive Peak Forward Surge Current	I <sub>FSM</sub>	1.5			A
Power Dissipation	P <sub>d</sub>	200			mW
Thermal Resistance Junction to Ambient	R <sub>θJA</sub>	625			°C/W
Junction Temperature	T <sub>J</sub>	125			°C
Storage Temperature range	T <sub>stg</sub>	-55 to 125			

#### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V <sub>R</sub>	I <sub>R</sub> = 10 uA	V <sub>R</sub>			V
Forward voltage Drop	V <sub>FM</sub>	I <sub>F</sub> = 20 mA			0.37	
		I <sub>F</sub> = 200 mA			0.6	
Instantaneous Reverse current	I <sub>RM</sub>	V <sub>R</sub> = 30 V	1N5819WSB		5	uA
		V <sub>R</sub> = 20 V	1N5818WSB			
		V <sub>R</sub> =10 V	1N5817WSB			
Total capacitance	C <sub>T</sub>	V <sub>R</sub> = 0 V, f= 1 MHz	10			pF
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> =I <sub>R</sub> =200mA, I <sub>rr</sub> =0.1xI <sub>R</sub> , R <sub>L</sub> =100Ω	50			ns

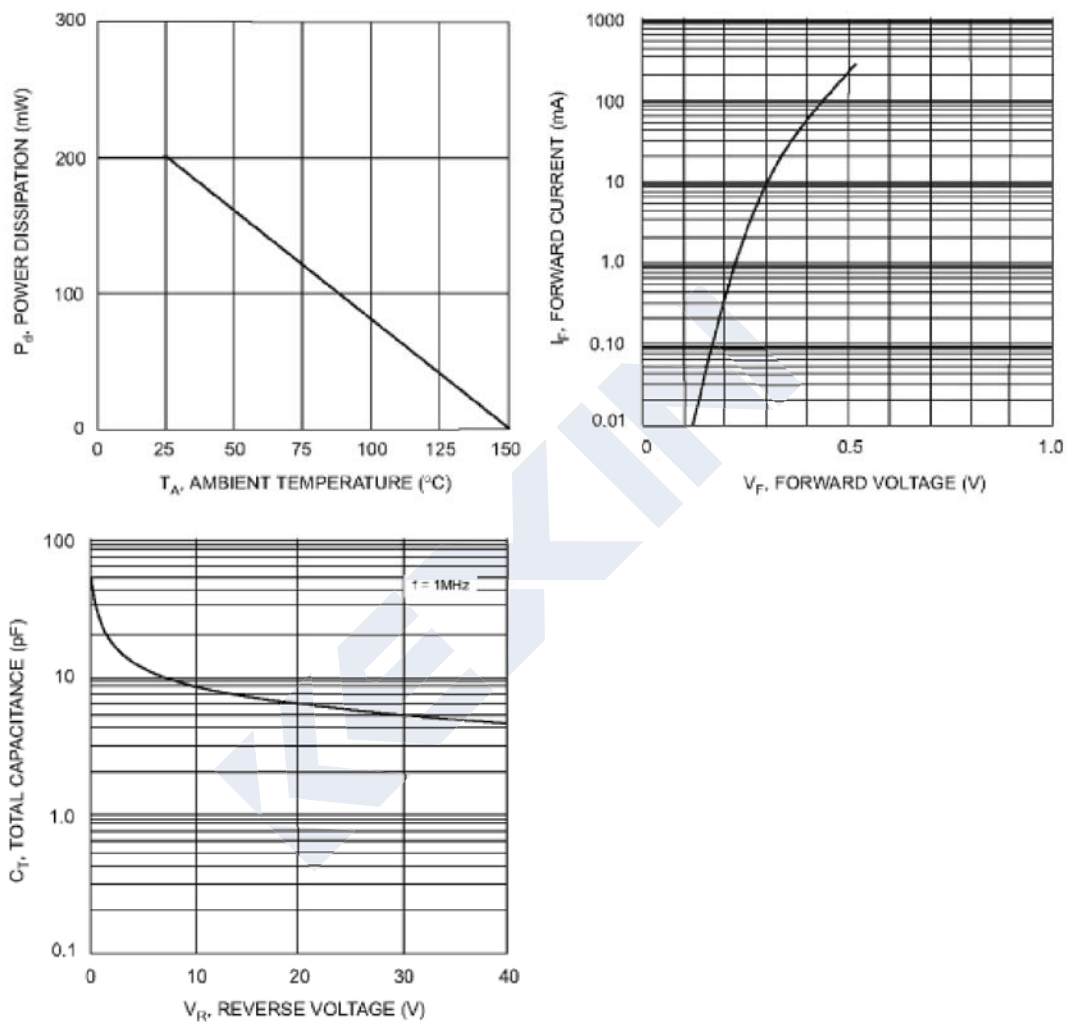
#### ■ Marking

Model	1N5819WSB	1N5818WSB	1N5817WSB
Marking	S4	S5	S6

## Schottky Diodes

### 1N5817WSB-1N5819WSB

#### ■ Typical Characteristics



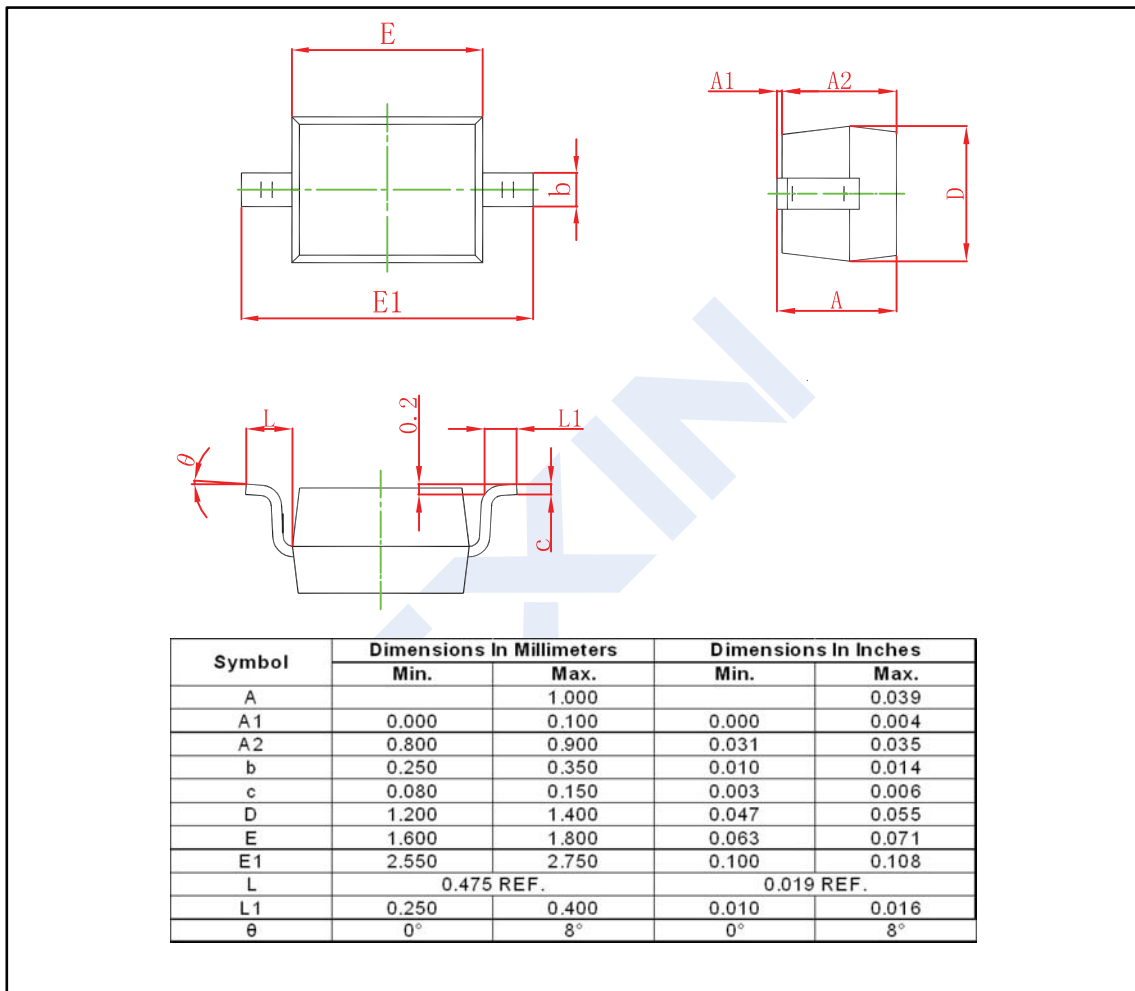
## Schottky Diodes

### 1N5817WSB-1N5819WSB

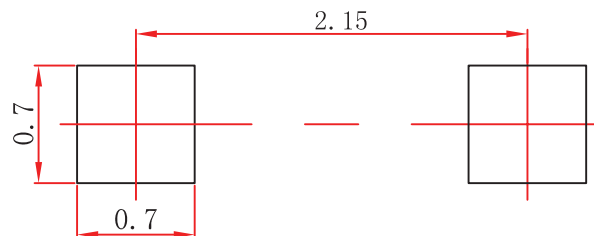
#### ■ Package Outline Dimensions

Plastic surface mounted package; 2 leads

SOD-323



#### ■ The Recommended Mounting Pad Size



#### Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.